



**BSS84** 

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-50V	10Ω @ V <sub>GS</sub> = -5V	-130mA

### Description

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(on)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# Applications

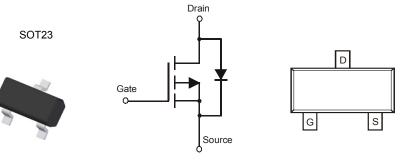
- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

### **Features and Benefits**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

# **Mechanical Data**

- Case: SOT23
- Case Material: UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (Lead Free Plating) Solderable per MIL-STD-202, Method 208 <sup>(3)</sup>
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



Top View



Top View

#### Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
BSS84-7-F	Commercial	SOT23	3000/Tape & Reel
BSS84Q-7-F	Automotive	SOT23	3000/Tape & Reel
BSS84-13-F	Commercial	SOT23	10000/Tape & Reel
BSS84Q-13-F	Automotive	SOT23	10000/Tape & Reel

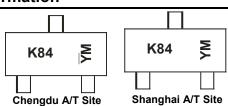
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

#### **Marking Information**



K84 = Product Type Marking Code

<u>YM</u> = Date Code Marking for SAT (Shanghai Assembly/ Test site) <u>YM</u> = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or  $\overline{Y}$  = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Date Code Key

Notes:

Year	1998	1999	2000	2001	2002	2003	2004		2011	2012	2013	2014	2015	2016	2017
Code	J	K	L	М	Ν	Р	R		Y	Z	Α	В	С	D	Е
					•										•
Month	Jan	Fe	b	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Oc	t I	Nov	Dec



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	-50	V
Drain-Gate Voltage $R_{GS} \le 20 K\Omega$		V <sub>DGR</sub>	-50	V
Gate-Source Voltage	Continuous	V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	Continuous	I <sub>D</sub>	-130	mA
Pulsed Drain Current		I <sub>DM</sub>	-1.2	А

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	PD	300	mW
Thermal Resistance, Junction to Ambient	$R_{ ext{ heta}JA}$	417	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					•	•
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-50	_	_	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
		_	_	-1	μA	V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C
Zero Gate Voltage Drain Current	IDSS	_	—	-2	μA	V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V, T <sub>J</sub> = +125°C
			—	-100	nA	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C
Gate-Body Leakage	I <sub>GSS</sub>	_	_	±10	nA	$V_{GS}$ = ±20V, $V_{DS}$ = 0V
ON CHARACTERISTICS (Note 6)			_			
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.8	_	-2.0	V	$V_{DS} = V_{GS}, I_D = -1mA$
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	_	_	10	Ω	V <sub>GS</sub> = -5V, I <sub>D</sub> = -0.100A
Forward Transconductance	<b>g</b> Fs	0.05	_	—	S	V <sub>DS</sub> = -25V, I <sub>D</sub> = -0.1A
DYNAMIC CHARACTERISTICS (Note 7)	• -		•		•	·
Input Capacitance	Ciss	_	_	45	pF	
Output Capacitance	Coss	_	_	25	pF	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	_	12	pF	]
SWITCHING CHARACTERISTICS (Note 7)	•				•	·
Turn-On Delay Time	t <sub>D(ON)</sub>	_	10	_	ns	V <sub>DD</sub> = -30V, I <sub>D</sub> = -0.27A,
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	18	_	ns	R <sub>GEN</sub> = 50Ω, V <sub>GS</sub> = -10V

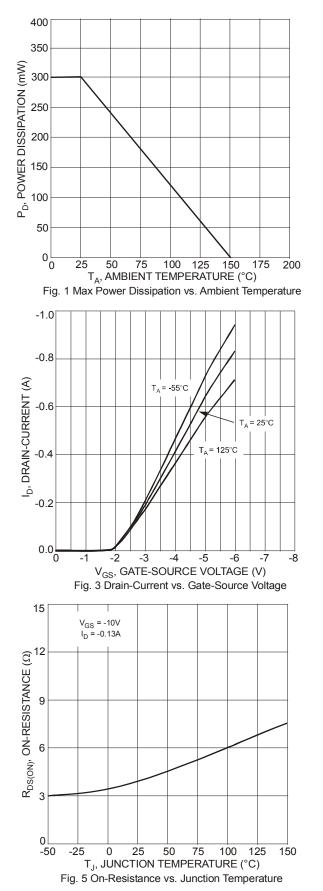
Notes: 5. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com.

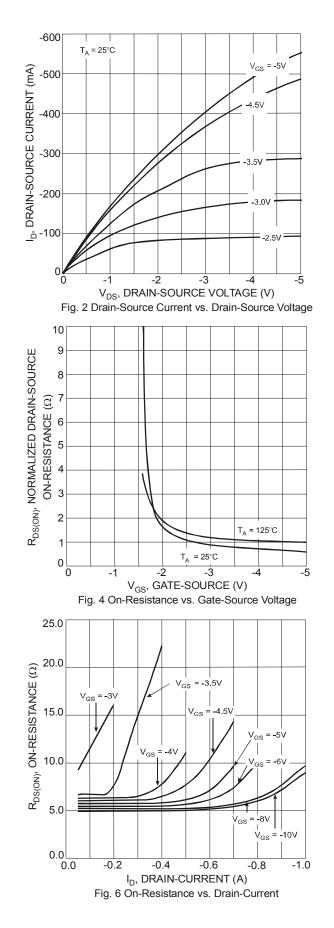
Short duration pulse test used to minimize self-heating effect.

7. Guaranteed by design. Not subject to production testing





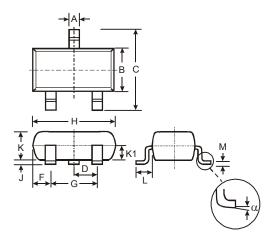






# **Package Outline Dimensions**

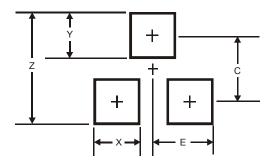
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
К	0.903	1.10	1.00				
K1	-	-	0.400				
L	0.45	0.61	0.55				
М	0.085	0.18	0.11				
α	0°	8°	-				
All	Dimens	ions in	mm				

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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